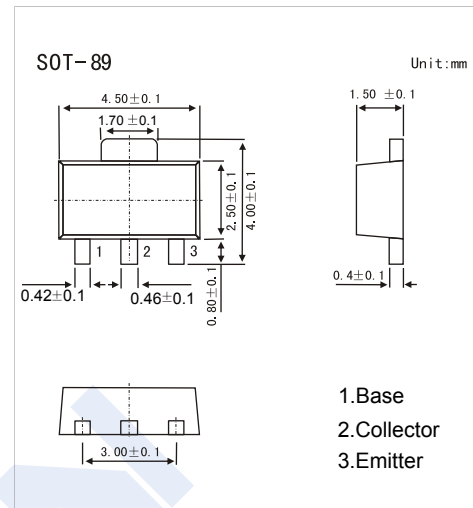


PNP Transistors

2SA1200

■ Features

- High Voltage : $V_{CEO} = -150V$
- High Transition Frequency : $f_r = 120MHz$ (typ.)
- Small Flat Package
- Complementary to 2SC2880



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-150	V
Collector-Base Voltage	V_{CB0}	-150	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-50	mA
Base Current	I_B	-10	mA
Collector Power Dissipation	P_C	500	mW
Jumction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

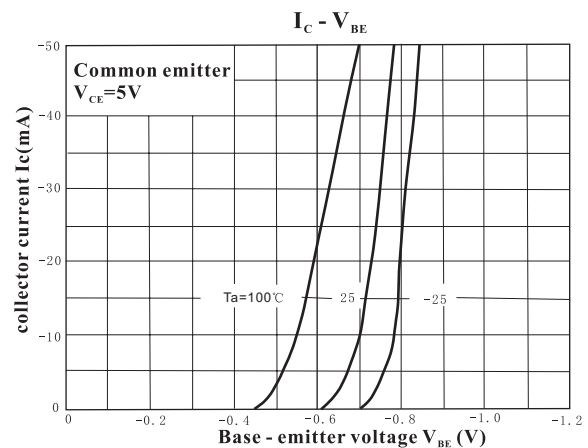
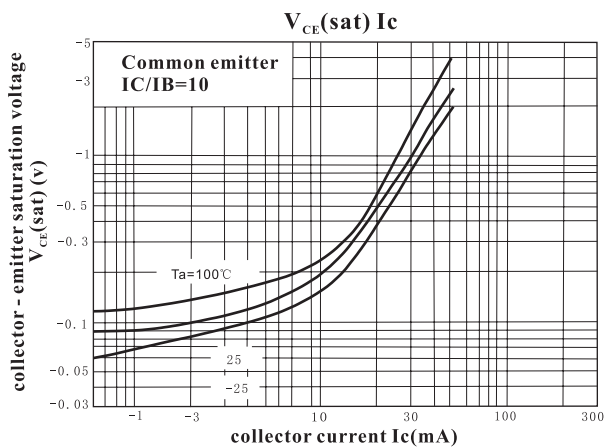
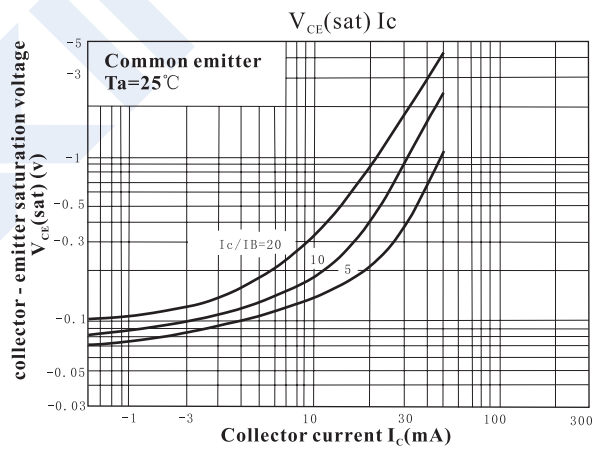
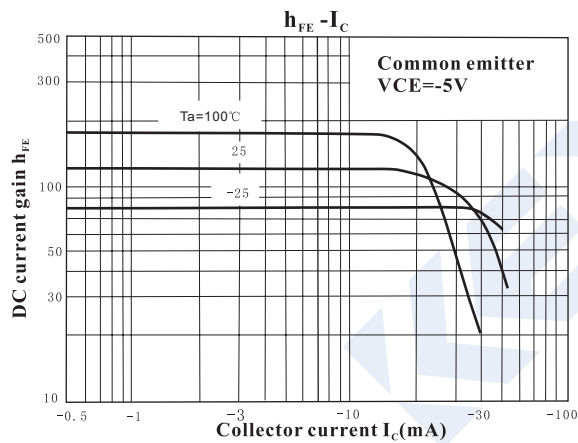
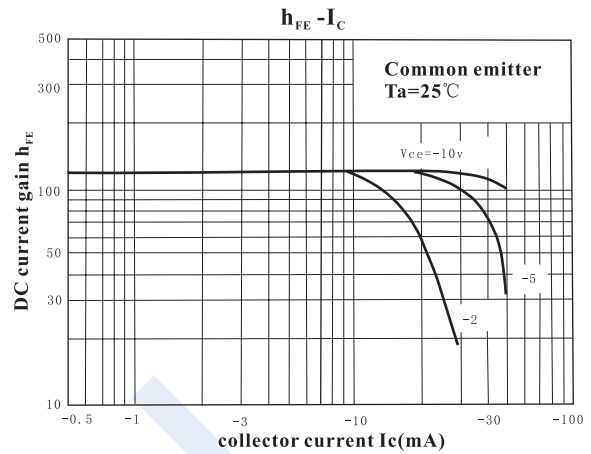
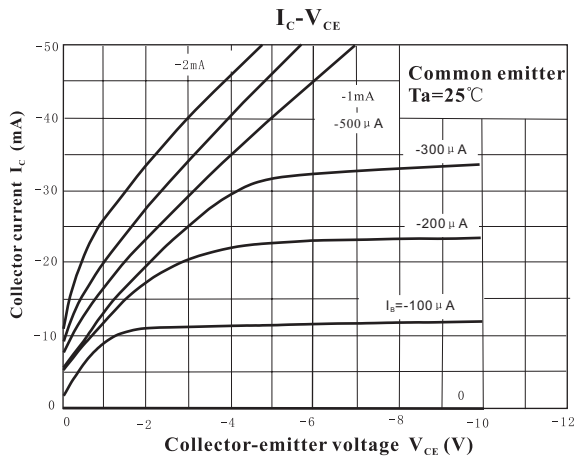
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\mu A, I_E = 0$	-150			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1\text{ mA}, I_B = 0$	-150			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -150\text{ V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$			-0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -30\text{ mA}$			-0.9	
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	70		240	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		4	5	pF
Transition frequency	f_r	$V_{CE} = -30\text{ V}, I_C = -10\text{ mA}$		120		MHz

■ Classification of h_{fe}

Type	2SA1200-O	2SA1200-Y
Range	70-140	120-240
Marking	BO	BY

2SA1200

Electrical Characteristics Curves



2SA1200

